

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|--|------------------------------------|-------------------|
| 1 | 1 | "6710391" | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 10:58 |
| 2 | 1 | "20040000686" | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 10:59 |
| 4 | 202 | houston-theodore-w.in. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 10:59 |
| 5 | 21 | houston-theodore-w.in. and DRAM and capacitor and ground | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 10:59 |
| 6 | 19 | (houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 10:59 |
| 7 | 5 | ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 10:59 |
| 8 | 5 | ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 10:59 |
| 9 | 2 | ("20010030338" "20020020883" "20020064065" and DRAM and ground | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | "2004/07/09 11:00 |
| 3 | 8 | ("20010030338" "20020020883" "20020064065" "USPAT; US-PGPUB; EPO; JPO; IBM_TDB | "2004/07/09 11:08 | |
| 10 | 660 | DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 11:09 |
| 11 | 406 | (DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 11:11 |
| 12 | 400 | ((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) (houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process) and (DRAM and heupton and heep and tewri and and DRAM and adtca and apao and toms and atf and foun and tham and etch\$4 and fomer and dv\$4) and dep and paa and q6 and planarizat\$5 and fth and heubt and math and ood and deswirne and DRAM and add gape and hot afi67 and 08 and 68 and 68 r houston and handope and awairmz\$5) (H0081006B008d0f"2002002088DRAM2and0064065" "6060351" "6204115" "6235603" "62 and aapadRAM and raaddgg and goundd) (H0081006B008d0f"2002002088" "DRAM0 and 64065" "6060351" "6204115" "6235603" "625 capacitor and ground) and (method or process)) (((houston-theodore-w.in. and | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 11:35 |
| 13 | 386 | DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 11:17 |

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capacitor and ground) and (method or

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| 23 | 0 | 20040012022.URPN. | USPAT | 2004/07/09 11:21 |
| 24 | 1 | "6562679".PN. | USPAT | 2004/07/09 11:25 |
| 25 | 0 | 6727542.URPN. | USPAT | 2004/07/09 11:25 |
| 26 | 9 | ("4864374" "5229326" "5998225" "6236079" "6297525" "6329684" "6352896" "6436762" "6555891").PN. | USPAT | 2004/07/09 11:26 |
| 27 | 0 | 6746915.URPN. | USPAT | 2004/07/09 11:27 |
| 28 | 0 | 6746915.URPN. | USPAT | 2004/07/09 11:27 |
| 29 | 55 | ((((((((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "62 and DRAM and ground) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "625 and (contact)) not (((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "62 and DRAM and ground) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "625 and (contact adj pillar)) and (method or process)) and (second adj (dielectric or insulati\$4))) and ((second adj (dielectric or insulati\$4)) with (etch\$4 or remov\$4))) and (capacitor with (plate or electrode))) and expos\$4) and (expos\$4 with (etch\$4 or remov\$4))) not | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 11:31 |
| 30 | 3 | memphi(y and (capacitor and (dielectric or insulati\$4) and (method or process)) and (second adj (dielectric or insulati\$4))) and (capacitor with (plate or electrode))) and expos\$4) and (expos\$4 with (etch\$4 or remov\$4))) not | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/07/09 11:34 |
| 31 | 10 | dfr498488d"gate504589"67103915248" "8009800686"6b60356M-thë6204115"im. "(5025668"the86056169fn! 46d29888"and 86pae295r and290046d30338" "2b026620880dfrë2002n0064d6DRAMPNnd | USPAT | 2004/07/09 11:33 |
| 32 | 0 | 63paa9f0WRAAnd ground) and (method or process)) (((houston-theodore-w.in. and | USPAT | 2004/07/09 11:34 |

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((method or process)) and planariz\$5)
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process)) and planariz\$5)

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|----|-----|--|------------------------------------|---------------------|
| 33 | 534 | memory and capacitor and (contact or plug) and (ground adj (plate or electrode)) | USPAT; US-PGPUB; EPO; JPO; IBM TDB | 2004/07/09 11:35 |
| 34 | 526 | (memory and capacitor and (contact or plug) and (ground adj (plate or electrode))) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "62 and DRAM and ground) (("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "625 (((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planariz\$5) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "62 and DRAM and ground) (("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "625 and (contact adj pillar)) ((((((((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) (houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) (((("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "62 and DRAM and ground) (("20010030338" "20020020883" "20020064065" "6060351" "6204115" "6235603" "625 and (contact)) not (((DRAM and ground and capacitor and ((dielectric or insulat\$4) with (etch\$4 or remov\$4) and planari\$6)) and (trench and substrate) and source and drain and gate) not ("6710391" "20040000686" houston-theodore-w.in. (houston-theodore-w.in. and DRAM and capacitor and ground) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) ((houston-theodore-w.in. and DRAM and capacitor and ground) and (method or process)) and planarizat\$5) | USPAT; US-PGPUB; EPO; JPO; IBM TDB | 2004/07/09 11:36 |

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capacitor and ground) and
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process; and planar (page 7)
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